

HCF4053B

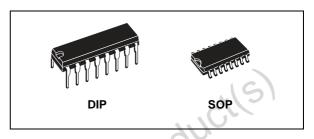
TRIPLE 2-CHANNEL ANALOG MULTIPLEXER/DEMULTIPLEXER

- LOW "ON" RESISTANCE : 125Ω (Typ.) OVER 15V p.p SIGNAL-INPUT RANGE FOR V_{DD} - V_{EE} = 15V
- HIGH "OFF" RESISTANCE : CHANNEL LEAKAGE ± 100pA (Typ.) at V_{DD} - V_{EE} = 18V
- BINARY ADDRESS DECODING ON CHIP
- HIGH DEGREE OF LINEARITY : < 0.5% DISTORTION TYP. at f_{IS} = 1KHz, V_{IS} = 5 V_{pp} , V_{DD} - $V_{SS} \ge$ 10V, RL = 10KΩ
- VERY LOW QUIESCENT POWER DISSIPATION UNDER ALL DIGITAL CONTROL INPUT AND SUPPLY CONDITIONS : 0.2 μW (Typ.) at V_{DD} - V_{SS} = V_{DD} - V_{EE} =10V
- MATCHED SWITCH CHARACTERISTICS : R_{ON} = 5Ω (Typ.) FOR V_{DD} - V_{EE} = 15V
- WIDE RANGE OF DIGITAL AND ANALOG SIGNAL LEVELS : DIGITAL 3 to 20, ANALOG TO 20V p.p.
- QUIESCENT CURRENT SPECIF. UP TO 20V
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT LEAKAGE CURRENT
 I₁ = 100nA (MAX) AT V_{DD} = 18V T_A = 25°C
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC JESD13B " STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES"

DESCRIPTION

The HCF4053B is a monolithic integrated circuit fabricated in Metal Oxide Semiconductor

PIN CONNECTION



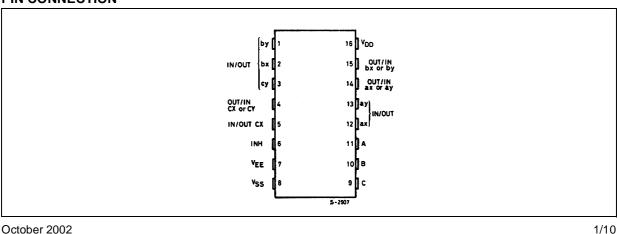
ORDER CODES

TUBE	T & R							
HCF4053BEY								
HCF4053BM1	HCF4053M013TR							
	TUBE HCF4053BEY							

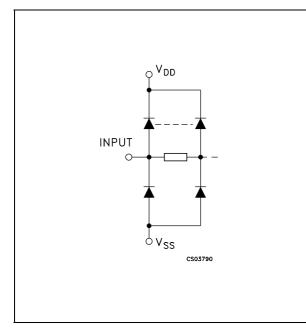
technology available in DIP and SOP packages.

The HCF4053B analog multiplexer/demultiplexer is a digitally controlled analog switch having low ON impedance and very low OFF leakage current. This multiplexer circuit dissipate extremely low quiescent power over the full V_{DD} - V_{SS} and V_{DD} - V_{EE} supply voltage range, independent of the logic state of the control signals.

When a logic "1" is present at the inhibit input terminal all channel are off. This device is a triple 2-channel multiplexer having three separate digital control inputs, A, B, and C, and an inhibit input. Each control input selects one of a pair of channels which are connected in a single pole double-throw configuration.



INPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

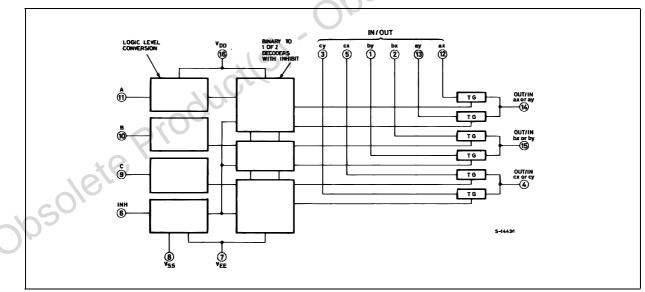
PIN No	SYMBOL	NAME AND FUNCTION
11, 10, 9	A, B, C	Binary Control Inputs
6	INH	Inhibit Inputs
12, 13, 2, 1 5, 3	' IN/OUT	ax,ay,bx,by,cx,cy Input/ Output
14	OUT/IN	ax or ay
15	OUT/IN	bx or by
4	OUT/IN	cx or cy
7	V _{EE}	Supply Voltage
8	V _{SS}	Negative Supply Voltage
16	V _{DD}	Positive Supply Voltage
TRUTH TA	BLE	AUCIL
INHIBIT	C or B or A	~~

TRUTH TABLE

INHIBIT	C or B or A	00.
0	0	ax or bx or cx
0		ay or by or cy
1	X	NONE

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X : Don't Care



FUNCTIONAL DIAGRAM

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage	-0.5 to +22	V
VI	DC Input Voltage	-0.5 to V _{DD} + 0.5	V
l _l	DC Input Current	± 10	mA
PD	Power Dissipation per Package	500 (*)	mW
	Power Dissipation per Output Transistor	100	mW
T _{op}	Operating Temperature	-55 to +125	°C
T _{stg}	Storage Temperature	-65 to +150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is JAN UCILS not implied.

All voltage values are referred to V_{SS} pin voltage. (*) 500mW at 65 $^\circ C$; derate to 300mW by 10mW/ $^\circ C$ from 65 $^\circ C$ to 85 $^\circ C$

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage	3 to 20	V
VI	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature	-55 to 125	°C
205016	ste Product(s) - Obs		

HCF4053B

DC SPECIFICATIONS

		Test Condition				Value							
Symbol	Parameter	V _{IS}	V _{EE}	v _{ss}		т	T _A = 25°C		-40 to 85°C		-55 to 125°C		Unit
		(V)	(V)	(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
١L	Quiescent Device				5		0.04	5		150		150	
	Current (all				10		0.04	10		300		300	
	switches ON or all switches OFF)				15		0.04	20		600		600	μΑ
					20		0.08	100		3000		3000	
SWITCH													
R _{ON}	Resistance	0 <u><</u> V _I ≤			5		470	1050		1200		1200	
		V_{DD}	0	0	10		180	400		520		520	Ω
		- 00			15		125	280		360		360	U.
Δ_{ON}	Resistance Δ_{RON}	0 <u><</u> V _I ≤			5		10						
	(between any 2 of	V _{DD}	0	0	10		10				5		Ω
	4 switches)	DD			15		5		-	\mathbf{O}^{\vee}	-		
OFF*	Channel Leakage Current (All Channel OFF) (COMMON O/I)		0	0	18		±0.1	100	21	1000		1000	nA
OFF*	Channel Leakage Current (Any Channel OFF)		0	0	18	S	±0.1	100		1000		1000	nA
CI	Input Capacitance					Y	5						
CO	Output Capacitance		-5	-5	5		9						pF
CIO	Feed through		10	61			0.2						
CONTRO	DL (Address or Inhi	bit)	11										
V _{IL}	Input Low Voltage	$ \gamma \rangle \rangle$		= V _{SS}	5			1.5		1.5		1.5	
				1KΩ	10			3		3		3	V
	21	= VDD		√ _{SS}	15			4		4		4	
V _{IH}	Input High Voltage	thru 1KΩ	l _{IS} <	2μΑ	5	3.5			3.5		3.5		
	×C)			I OFF	10	7			7		7		V
			chan	nels)	15	11			11		11		
I _{IH} , I _{IL}	Input Leakage Current	VI	= 0/18\	/	18		±10 ⁻³	±0.1		±1		±1	μΑ
CI	Input Capacitance						5	7.5					pF

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* Determined by minimum feasible leakage measurement for automating testing.

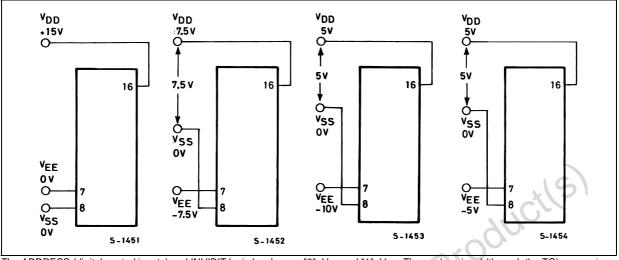
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}C$, $C_{L} = 50pF$, all input square wave rise and fall time = 20 ns)

				Test Co	ondition				Value		Unit
Parameter	V _{EE} (V)	R L (ΚΩ)	f _l (KHz)	V _I (∀)	V _{SS} (V)	V _{DD} (∀)		Min.	Тур.	Max.	
Propagation Delay				V		5			30	60	
Time (signal input to		200				10			15	30	ns
output)						15			11	20	
Frequency Response Channel "ON" (sine wave input) at	= V _{SS}	1		5(*)		10	V _O at Common OUT/IN		25		MHz
$20 \log V_O/V_I = -3dB$							V _O at any channel		60	G	
Feed through (all channels OFF) at	= V _{SS}	1		5(*)		10	V _O at Common OUT/IN		10		MHz
$20 \log V_{\rm O}/V_{\rm I} = -40 \rm dB$	- • 55	1		5()		10	V _O at any channel	0	8		
Frequency Signal Crosstalk at	= V _{SS}	1		5(*)		10	Between any 2 Sections (IN pin 2, OUT pin 14)		2.5		MHz
$20 \log V_O/V_I = -40 dB$	- • 55			3()	C		Between any 2 Sections (IN pin 15, OUT pin 14)		6		
Sine Mayo Distortion				2(*)	N.	5			0.3		
Sine Wave Distortion f _{IS} = 1KHz Sine Wave	$= V_{SS}$	10	1	3(*)		10			0.2		%
				5(*)		15			0.12		
CONTROL (Address	or Inhibi	t)									
Propagation Delay:	0		х С	1	0	5			360	720	
Address to Signal	0				0	10			160	320	ns
OUT (Channels ON or OFF)	0	γO			0	15			120	240	115
	-5				0	5			225	450	
Propagation Delay:	0				0	5			360	720	
Inhibit to Signal OUT	0	1			0	10			160	320	ns
(Channel turning ON)	0				0	15			120	240	115
	-10				0	5			200	400	
Propagation Delay:	0					5	Ī		200	450	
Inhibit to Signal OUT	0	10				10	1		90	210	
(Channel turning	0	10				15	1		70	160	ns
OFF)	-10					5	1		130	300	1
Address or Inhibit to Signal Crosstalk	0	10 ⁽¹⁾			0	10	V _C = V _{DD} -V _{SS} (square wave)		65		mV peak

(1) Both ends of channel. * Peak to Peak voltage symmetrical about (V_DD - V_EE) /2

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TYPICAL BIAS VOLTAGES



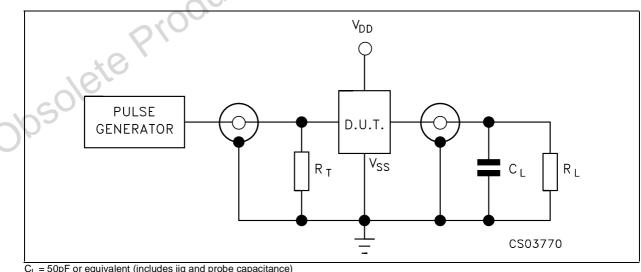
The ADDRESS (digital-control inputs) and INHIBIT logic levels are : "0"=V_{SS} and "1"=V_{DD}. The analog signal (through the TG) may swing from V_{EE} to V_{DD}

SPECIAL CONSIDERATIONS

Control of analog signals up to 20V peak to peak can be achieved by digital signal amplitudes of 4.5 to 20V (if $V_{DD} - V_{SS} = 3V$, a $V_{DD} - V_{EE}$ of up to 13V can be controlled; for $V_{DD} - V_{EE}$ level differences above 13V, a $V_{DD} - V_{SS}$ of at least 4.5V is required. For example, if $V_{DD} = +5$, $V_{SS} = 0$, and $V_{EE} = -13.5$, analog signals from -13.5V to 4.5V can be controlled by digital inputs of 0 to 4.5V. In

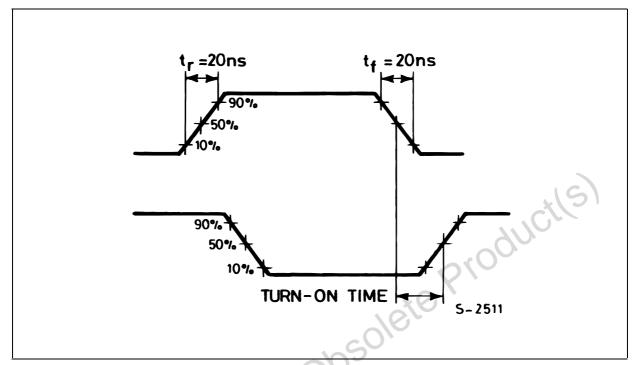
certain applications, the external load resistor current may include both $\rm V_{DD}$ and signal-line components. To avoid drawing $\rm V_{DD}$ current when switch current flows into the transmission gate inputs, the voltage drop across the bidirectional switch must not exceed 0,8V (calculated from RON values shown in DC SPECIFICATIONS). No VDD current will flow through R_L if the switch current flows into leads 4, 14 and 15.

TEST CIRCUIT



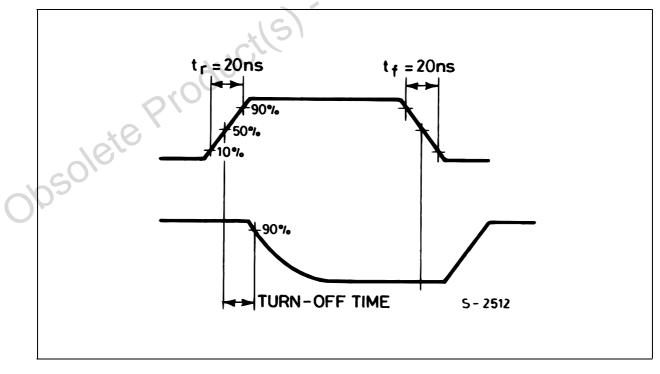
 $C_L = 50pF$ or equivalent (includes jig and probe capacitance)

 $R_L = 200 K\Omega$ $R_T = Z_{OUT}$ of pulse generator (typically 50 Ω)



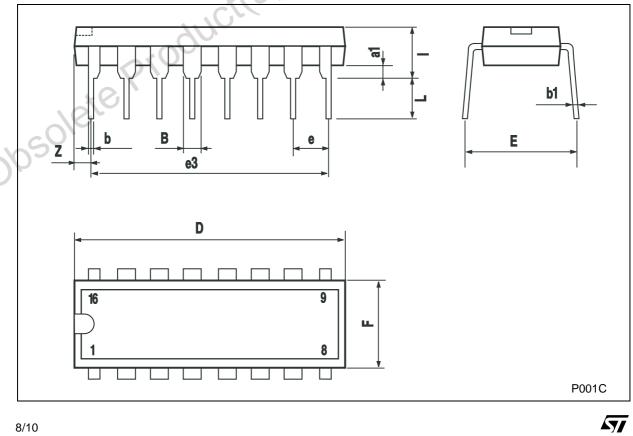
WAVEFORM 1 : CHANNEL BEING TURNED ON ($R_L = 1K\Omega$, f=1MHz; 50% duty cycle)

WAVEFORM 2 : CHANNEL BEING TURNED OFF ($R_L = 1K\Omega$, f=1MHz; 50% duty cycle)



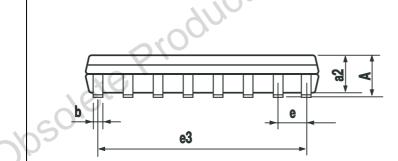
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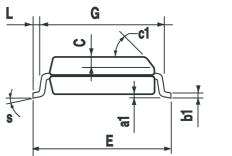
	Plastic DIP-16 (0.25) MECHANICAL DATA									
DIM.		mm.		inch						
DIM.	MIN.	ТҮР	MAX.	MIN.	TYP.	MAX.				
a1	0.51			0.020						
В	0.77		1.65	0.030		0.065				
b		0.5			0.020					
b1		0.25			0.010	16				
D			20		. (0.787				
Е		8.5			0.335					
е		2.54			0.100					
e3		17.78		× 0,	0.700					
F			7.1	1610		0.280				
I			5.1	0.		0.201				
L		3.3	Oh-		0.130					
Z			1.27			0.050				

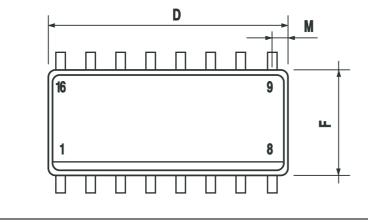


DIM.		mm.		inch				
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
А			1.75			0.068		
a1	0.1		0.2	0.003		0.007		
a2			1.65			0.064		
b	0.35		0.46	0.013		0.018		
b1	0.19		0.25	0.007		0.010		
С		0.5			0.019	15		
c1		·	45° ((typ.)	. (1		
D	9.8		10	0.385	YU.	0.393		
Е	5.8		6.2	0.228	×0.	0.244		
е		1.27			0.050			
e3		8.89		*0	0.350			
F	3.8		4.0	0.149		0.157		
G	4.6		5.3	0.181		0.208		
L	0.5		1.27	0.019		0.050		
М			0.62			0.024		

SO-16 MECHANICAL DATA







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